

### • General Description

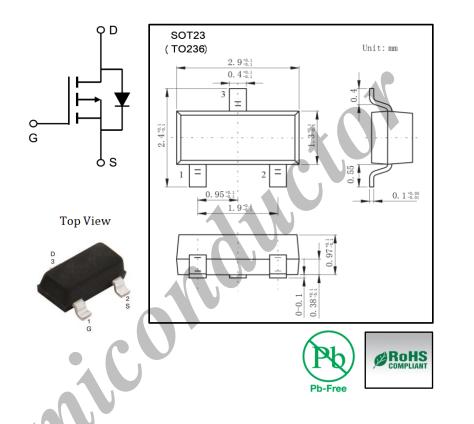
AP3409A combines advanced MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is most suitable to load-switch or PWM applications.

### • Applications

DC/DC converter for portable devicesLoad switch

# Product Summary

VDS	-30V
ID (at $V_{GS} = -10V$ )	-2.6A
$R_{DS(ON)}$ (at $V_{GS} = -10V$ )	<130mΩ
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$ )	< 200mΩ



## • Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-30	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	V	
Continuous Drain Current T <sub>A</sub> =25°C		-2.6		
T <sub>A</sub> =70°C	Ι <sub>D</sub>	-2.2	А	
Pulsed Drain Current *	I <sub>DM</sub>	-20		
Power Dissipation T <sub>A</sub> = 25°C	P <sub>n</sub>	1.4	W	
T <sub>A</sub> = 70°C		1		
Thermal Resistance. Junction-to-Ambient $t \le 10s$	R <sub>θJA</sub>	90		
Thermal Resistance. Junction-to-Ambient (Stead-state)		125	°C/W	
Thermal Resistance. Junction-to-Case (Stead-state)	R <sub>θJC</sub>	80		
Junction Temperature	٦J	150	°C	
Storage Temperature Range	Тѕтб	-55 to 150	۰L	

\* Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25°C.



#### • Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30			V	
Zero Gate Voltage Drain Current	Ţ	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μΑ	
	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C			-5		
Gate-Body leakage current	I <sub>GSS</sub>	$V_{DS}=0V$ , $V_{GS}=\pm 20V$			±100	nA	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.9	-3	V	
Static Drain-Source On-Resistance		V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.6A		97	130		
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.6A T <sub>J</sub> =125°C		135	150	mΩ	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A		166	200		
On state drain current	I <sub>D(ON)</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-5			А	
Forward Transconductance	$\mathbf{g}_{\mathrm{FS}}$	V <sub>DS</sub> =-5V, I <sub>D</sub> =-5A	3	3.8		S	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		302	370	pF	
Output Capacitance	Coss			50.3			
Reverse Transfer Capacitance	C <sub>rss</sub>			37.8			
Gate Resistance	Rg	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		12	18	Ω	
Total Gate Charge (10V)			6.8	9			
Total Gate Charge (4.5V)	$Q_{g}$	-V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-2.6A		2.4		nC	
Gate Source Charge	Q <sub>gs</sub>	$V_{GS}$ 4.5 V, $V_{DS}$ 1.5 V, $I_D$ 2.0A		1.6			
Gate Drain Charge	Q <sub>gd</sub>			0.95			
Turn-On Delay Time	t <sub>D(on)</sub>			7.5			
Turn-On Rise Time	t <sub>r</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V,		3.2		ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	R <sub>L</sub> =5.8Ω, R <sub>GEN</sub> =3Ω		17			
Turn-Off Fall Time	t <sub>f</sub>	<u> </u>		6.8		]	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-2.6A, d <sub>I</sub> /d <sub>t</sub> =100A/ μs		16.8	22		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =-2.6A, d <sub>I</sub> /d <sub>t</sub> =100A/ μs		10		nC	
Maximum Body-Diode Continuous Current	Is				-2	А	
Diode Forward Voltage	V <sub>SD</sub>	$I_{S}$ =-1A, $V_{GS}$ =0V		-0.82	-1	V	

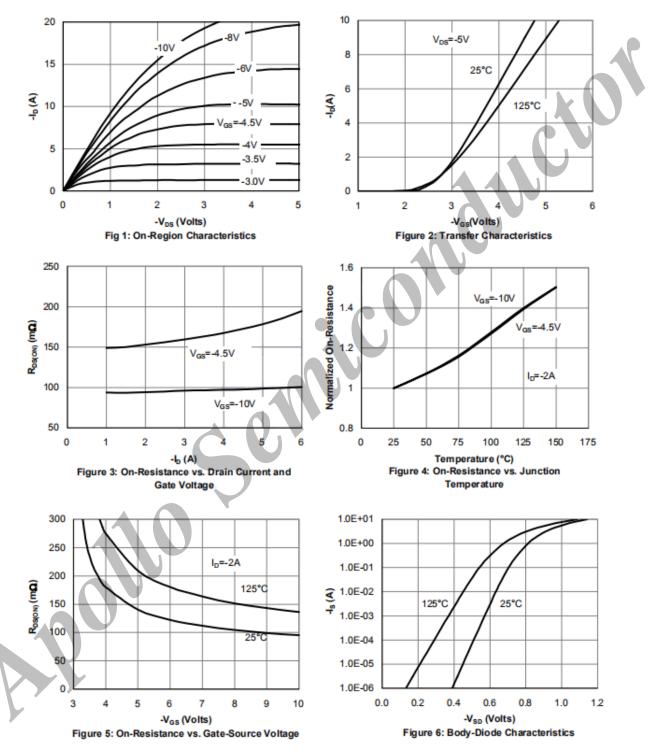
#### • Ordering Information

Ordering Part Number	Package	MOQ
AP3409A	SOT23 (TO236)	3,000 pcs / reel

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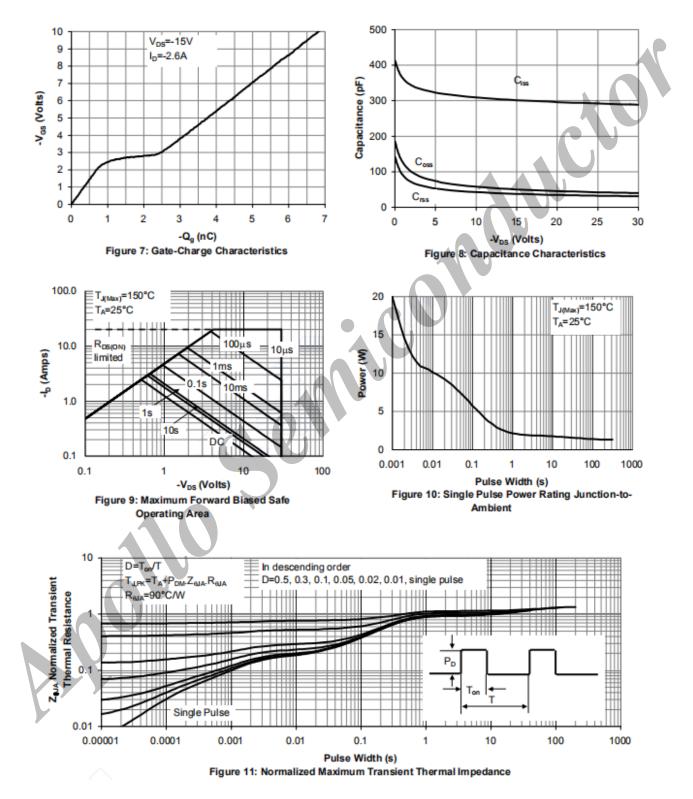
• Typical Characteristics



The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.



#### **Typical Characteristics**





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